

REMARKS

Reconsideration of the above identified application in view of the preceding amendments and following remarks is respectfully requested.

Claims 1-9 are pending in this application. By this Amendment, Applicants have added Claim 9 by this amendment. It is respectfully submitted that no new matter has been introduced by these amendments, as support therefor is found throughout the specification and drawings.

In the Office Action, Claims 1, 2, 7 and 8 were rejected under 35 U.S.C. §102(a) over the applicant's admitted prior art (AAPA). The Examiner's grounds for rejection are herewith traversed, and reconsideration is respectfully requested.

The AAPA discloses a power transistor with an N⁺ type electrode layer 118, which is formed to surround a P⁺ type collector layer 106 as shown in Figure 3 of the subject application. The N⁺ type electrode layer 118 is outside the active region of the power transistor and does not pass through the N-type epitaxial layer 104 to the N⁺ type buried layer 102.

In contrast, Claim 1 recites a power transistor composed of a plurality of vertical PNP transistors formed on a P-type silicon substrate, wherein a singularity or plurality of electrode portions of an N⁺ type buried layer formed to isolate the P-type silicon substrate and the plurality of vertical PNP transistors from each other are provided in an active region of the power transistor. The AAPA does not disclose or suggest such a structural configuration of providing the electrode portions in the active region. Accordingly, Claim 1 and each of the remaining claims depending therefrom, namely Claims 1-7, distinguish the subject invention from the AAPA.

Regarding Claim 8, it includes each limitation of Claim 1 by reference. Consequently, Claim 8 distinguish the subject invention from the AAPA for the same reasons. In view of the above, withdrawal of the rejection is respectfully requested.

In the Office Action, Claims 5 and 6 were rejected under 35 U.S.C. § 103 (a) over the AAPA in view of U.S. Patent No. 5,648,281 to Williams et al. The Examiner's grounds for rejection are herewith traversed, and reconsideration is respectfully requested.

As noted above, the AAPA discloses a power transistor the N⁺ type electrode layer 118 outside the active region of the power transistor.

Similarly, Williams et al. disclose an N⁺ sinker 348 extending down from the surface of the wafer to the N buried layer 340. However, the N⁺ sinker 348 is outside the active region of the power transistor.

It is respectfully submitted that Williams et al. do not overcome the deficiencies of the AAPA, as noted above with respect to Claim 1 and in the specification itself. In particular, neither the AAPA nor Williams et al. disclose or suggest, either alone or in combination, in whole or in part, a power transistor including, *inter alia*, a plurality of vertical PNP transistors, wherein a singularity or plurality of electrode portions of an N⁺ type buried layer formed to isolate the P-type silicon substrate and the plurality of vertical PNP transistors from each other are provided in an active region of the power transistor. Accordingly, Claim 1 and each of the claims depending therefrom are not rendered obvious by the combination of references cited by the Examiner and withdrawal of the rejection under 35 U.S.C. §103 (a) is respectfully requested.

Applicant has added new Claim 9 which is directed to additional patentable aspects of the subject invention identified. New independent Claim 9 is

believed to be commensurate in scope with Claim 1 and as such it is believed that no additional searching is required. Applicants respectfully submit that new Claim 9 patentably distinguishes over the art of record for at least the same reason as noted above with respect to Claim 1, and, therefore, allowance is respectfully requested.

Any additional fees or overpayments due as a result of filing the present paper may be applied to Deposit Account No. 04-1105. It is respectfully submitted that all of the claims now remaining in this application, namely Claims 1-9, are in condition for allowance, and such action is earnestly solicited.

If after reviewing this amendment, the Examiner believes that a telephone interview would facilitate the resolution of any remaining matters the undersigned attorney may be contacted at the number set forth herein below.

Respectfully submitted,

Date: August 5, 2005


George N. Chaclas, Reg. No. 46,608
Edwards & Angell LLP
Attorney for Applicant
P.O. Box 55874
Boston, MA 02205
Tel: (401) 276-6653
Fax: (888) 325-1684
Email: gchaclas@edwardsangell.com